



# ZP2000- RECTIFIER DIODE

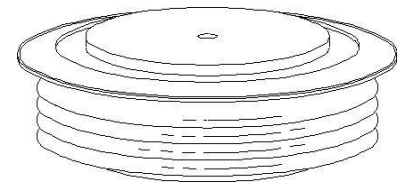
2600-3600V<sub>RRM</sub>

## GENERAL PURPOSE HIGH POWER STANDARD RECTIFIER

### Features:

- . All diffused structure
- . High surge rating
- . Blocking capability up to 3600 volts
- . Ceramic housing hermetic package
- . Pressure assembled device

D10C



## ELECTRICAL CHARACTERISTICS AND RATINGS

### Reverse Blocking

| Device Type | V <sub>RRM</sub> (1) | V <sub>RSM</sub> (1) |
|-------------|----------------------|----------------------|
| ZP2000-26   | 2600                 | 2700                 |
| ZP2000-28   | 2800                 | 2900                 |
| ZP2000-30   | 3000                 | 3100                 |
| ZP2000-32   | 3200                 | 3300                 |
| ZP2000-34   | 3400                 | 3500                 |
| ZP2000-36   | 3600                 | 3700                 |

V<sub>RRM</sub> = Repetitive peak reverse voltage

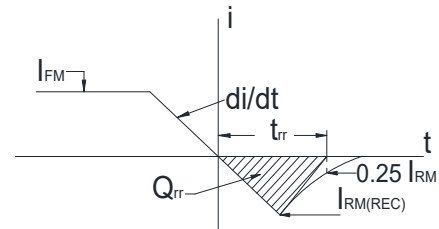
V<sub>RSM</sub> = Non repetitive peak reverse voltage (2)

|                                         |                  |                   |
|-----------------------------------------|------------------|-------------------|
| Repetitive peak reverse leakage current | I <sub>RRM</sub> | 5 mA<br>60 mA (3) |
|-----------------------------------------|------------------|-------------------|

Notes:

All ratings are specified for T<sub>j</sub>=25 °C, unless otherwise stated

- (1) All voltage ratings are specified for an applied 50Hz/60Hz sinusoidal waveform over the temperature range 0 to +150 °C.
- (2) 10 msec. max. pulse width
- (3) Maximum value for T<sub>j</sub> = 150 °C.
- (4) See parameter definition below :



reverse recovery characteristic

### Conducting - on state

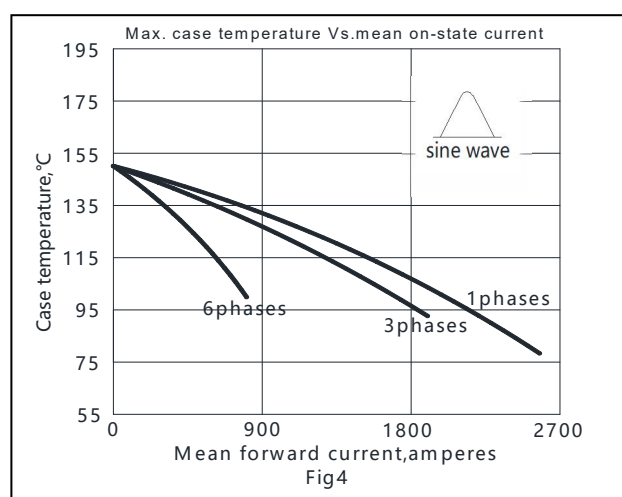
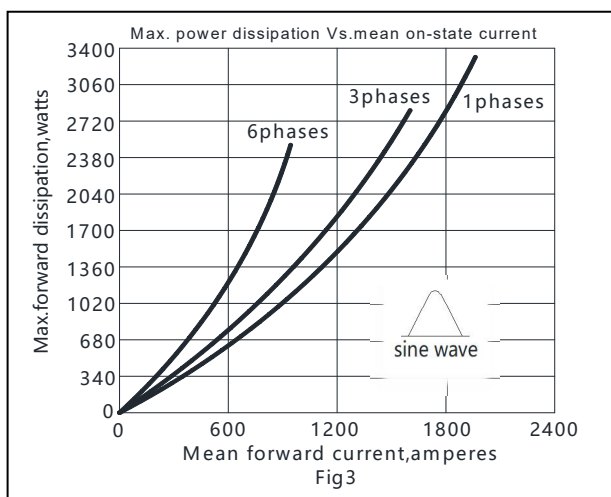
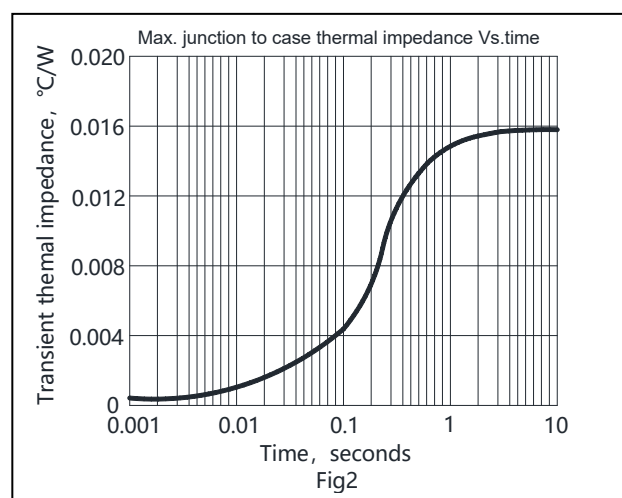
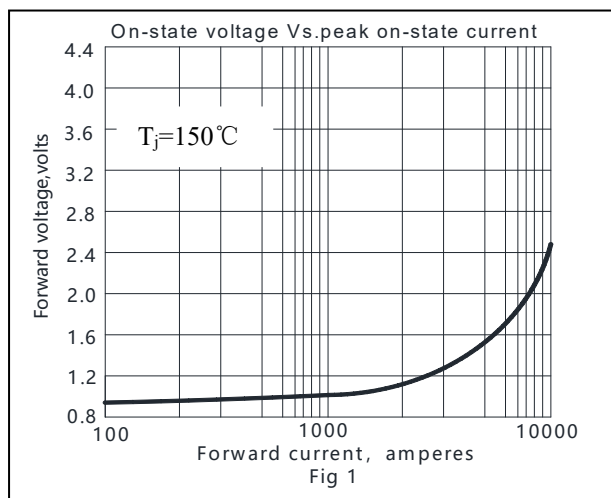
| Parameter                                     | Symbol               | Min. | Max.                | Typ. | Units            | Conditions                                                                    |
|-----------------------------------------------|----------------------|------|---------------------|------|------------------|-------------------------------------------------------------------------------|
| Average forward current                       | I <sub>F(AV)</sub>   |      | 2000                |      | A                | Sinewave 180°, T <sub>c</sub> =100°C                                          |
| RMS forward current                           | I <sub>FRMS</sub>    |      | 3140                |      | A                | Nominal value                                                                 |
| Peak one cycle surge (non repetitive) current | I <sub>FSM</sub>     |      | 28000               |      | A                | 10 msec (50Hz), sinusoidal wave-shape, 180° conduction, T <sub>j</sub> =150°C |
| I square t                                    | I <sup>2</sup> t     |      | 4 × 10 <sup>6</sup> |      | A <sup>2</sup> s | 10 msec                                                                       |
| Peak forward voltage                          | V <sub>FM</sub>      |      | 1.55                |      | V                | I <sub>FM</sub> = 3000A; T <sub>j</sub> =25°C                                 |
| Threshold voltage                             | V <sub>FO</sub>      |      | 0.86                |      | V                | T <sub>j</sub> =150°C, I=0.5 π I <sub>F(AV)</sub> to 1.5 π I <sub>F(AV)</sub> |
| Slope resistance                              | r <sub>F</sub>       |      | 0.16                |      | mΩ               | T <sub>j</sub> =150°C, I=0.5 π I <sub>F(AV)</sub> to 1.5 π I <sub>F(AV)</sub> |
| Reverse Recovery Current (4)                  | I <sub>RM(REC)</sub> |      |                     |      | A                | I <sub>FM</sub> = 500 A; di/dt = -10 A/s; T <sub>jmax</sub>                   |
| Reverse Recovery Charge (4)                   | Q <sub>rr</sub>      |      |                     | 5000 | μC               | I <sub>FM</sub> = 500 A; di/dt = -10 A/s; T <sub>jmax</sub>                   |
| Reverse Recovery Time (4)                     | t <sub>rr</sub>      |      |                     |      | μs               | I <sub>FM</sub> = 500 A; di/dt = -10 A/s; T <sub>jmax</sub>                   |

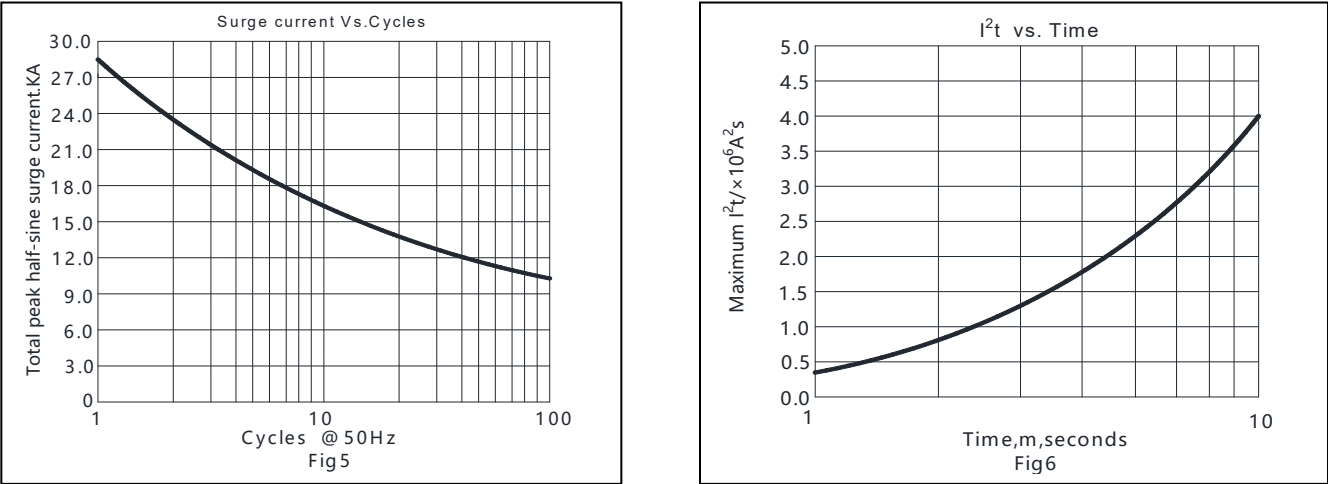
| Parameter                             | Symbol            | Min. | Max.   | Typ. | Units | Conditions          |
|---------------------------------------|-------------------|------|--------|------|-------|---------------------|
| Operating temperature                 | $T_j$             | -40  | +150   |      | °C    |                     |
| Storage temperature                   | $T_{stg}$         | -40  | +150   |      | °C    |                     |
| Thermal resistance - junction to case | $R_{\theta(j-c)}$ |      | 0.015  |      | °C/W  | Double sided cooled |
| Thermal resistance - case to heatsink | $R_{\theta(c-s)}$ |      | 0.0045 |      | °C/W  | Double sided cooled |
| Mounting force                        | F                 | 27   | 33     | 30   | kN    |                     |
| Weight                                | m                 |      |        | 0.72 | kg.   |                     |

\* Mounting surfaces smooth, flat and greaseless

## Graph

## ZP2000-RECTIFIER DIODE





CASE OUTLINE AND DIMENSIONS

